2N3903, 2N3904

2N3903 is a Preferred Device

General Purpose Transistors

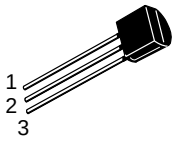
NPN Silicon

ON Semiconductor®

http://onsemi.com

Features

- Pb−Free Package May be Available. The G−Suffix Denotes a Pb−Free Lead Finish



TO−92
CASE 29
STYLE 1

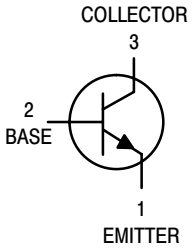
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	40	Vdc
Collector−Base Voltage	V_{CBO}	60	Vdc
Emitter−Base Voltage	V_{EBO}	6.0	Vdc
Collector Current − Continuous	I_C	200	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS (Note 1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	83.3	°C/W

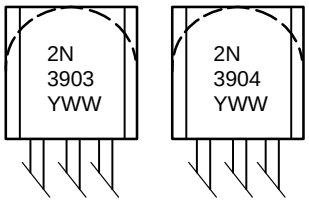
1. Indicates Data in addition to JEDEC Requirements.



STYLE 1

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MARKING DIAGRAMS



Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping†
2N3903	TO−92	5000 Units/Box
2N3903RLRM	TO−92	2000/Ammo Pack
2N3904	TO−92	5000 Units/Box
2N3904RLRA	TO−92	2000/Tape & Reel
2N3904RLRE	TO−92	2000/Tape & Reel
2N3904RLRM	TO−92	2000/Ammo Pack
2N3904RLRMG	TO−92	2000/Ammo Pack
2N3904RLRP	TO−92	2000/Ammo Pack
2N3904RL1	TO−92	2000/Tape & Reel
2N3904ZL1	TO−92	2000/Ammo Pack

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

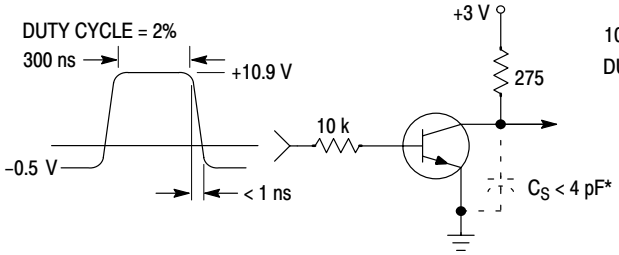
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

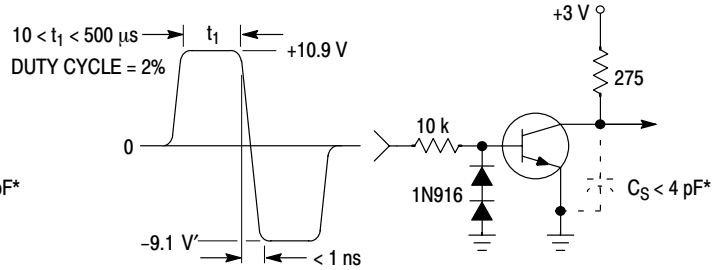
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector−Emitter Breakdown Voltage (Note 2) (I_C = 1.0 mAdc, I_B = 0)		$V_{(BR)CEO}$	40	−	Vdc
Collector−Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	60	−	Vdc
Emitter−Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	6.0	−	Vdc
Base Cutoff Current (V_{CE} = 30 Vdc, V_{EB} = 3.0 Vdc)		I_{BL}	−	50	nAdc
Collector Cutoff Current (V_{CE} = 30 Vdc, V_{EB} = 3.0 Vdc)		I_{CEX}	−	50	nAdc
ON CHARACTERISTICS					
DC Current Gain (Note 2)		h_{FE}			−
(I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc)	2N3903		20	−	
	2N3904		40	−	
(I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc)	2N3903		35	−	
	2N3904		70	−	
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)	2N3903		50	150	
	2N3904		100	300	
(I_C = 50 mAdc, V_{CE} = 1.0 Vdc)	2N3903		30	−	
	2N3904		60	−	
(I_C = 100 mAdc, V_{CE} = 1.0 Vdc)	2N3903		15	−	
	2N3904		30	−	
Collector−Emitter Saturation Voltage (Note 2)		$V_{CE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)			−	0.2	
(I_C = 50 mAdc, I_B = 5.0 mAdc			−	0.3	
Base−Emitter Saturation Voltage (Note 2)		$V_{BE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)			0.65	0.85	
(I_C = 50 mAdc, I_B = 5.0 mAdc)			−	0.95	
SMALL−SIGNAL CHARACTERISTICS					
Current−Gain − Bandwidth Product		f_T			MHz
(I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	2N3903		250	−	
	2N3904		300	−	
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	−	4.0	pF
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	−	8.0	pF
Input Impedance		h_{ie}			k Ω
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3903		1.0	8.0	
	2N3904		1.0	10	
Voltage Feedback Ratio		h_{re}			X 10^{-4}
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3903		0.1	5.0	
	2N3904		0.5	8.0	
Small−Signal Current Gain		h_{fe}			−
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3903		50	200	
	2N3904		100	400	
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{oe}	1.0	40	μmhos
Noise Figure		NF			dB
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 k Ω, f = 1.0 kHz)	2N3903		−	6.0	
	2N3904		−	5.0	

SWITCHING CHARACTERISTICS

Delay Time	(V_{CC} = 3.0 Vdc, V_{BE} = 0.5 Vdc, I_C = 10 mAdc, I_{B1} = 1.0 mAdc)		t_d	−	35	ns
Rise Time			t_r	−	35	ns
Storage Time	(V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = I_{B2} = 1.0 mAdc)	2N3903	t_s	−	175	ns
		2N3904		−	200	
Fall Time			t_f	−	50	ns

2. Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2%.





* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit

Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS

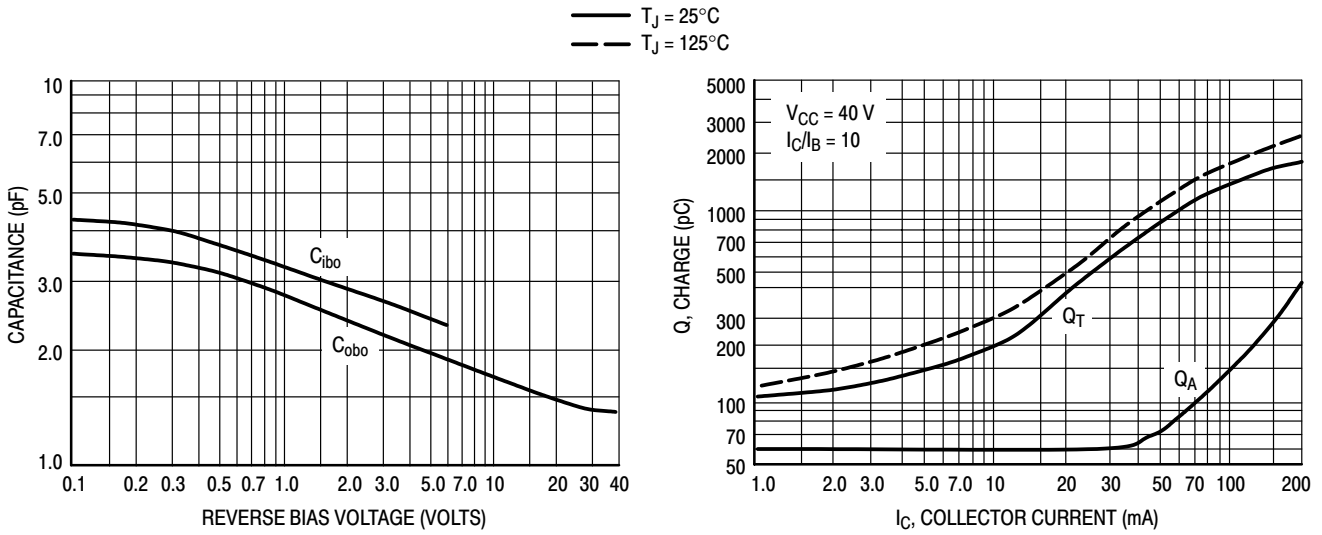


Figure 3. Capacitance

Figure 4. Charge Data

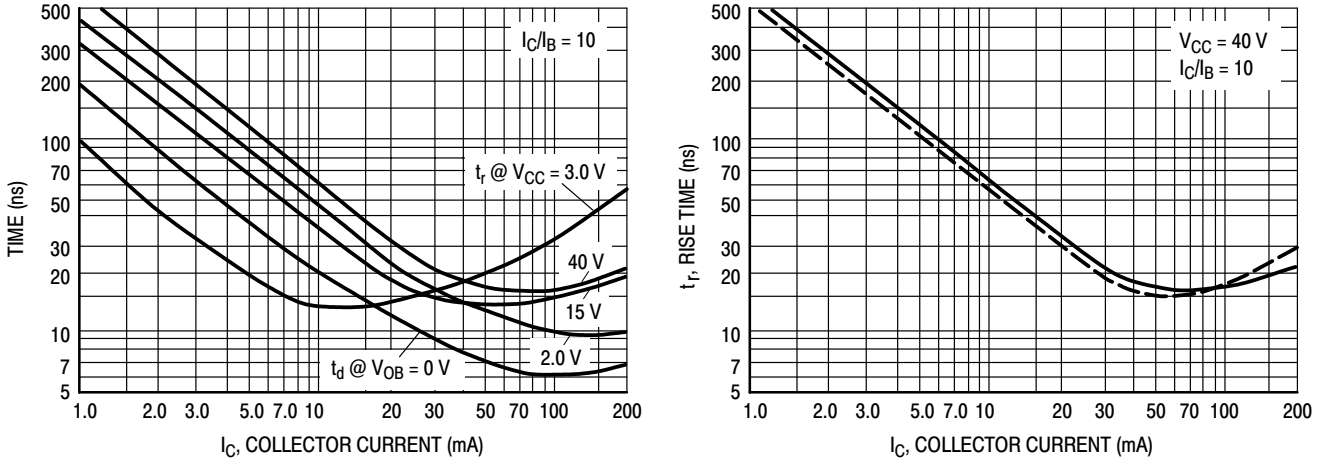


Figure 5. Turn−On Time

Figure 6. Rise Time

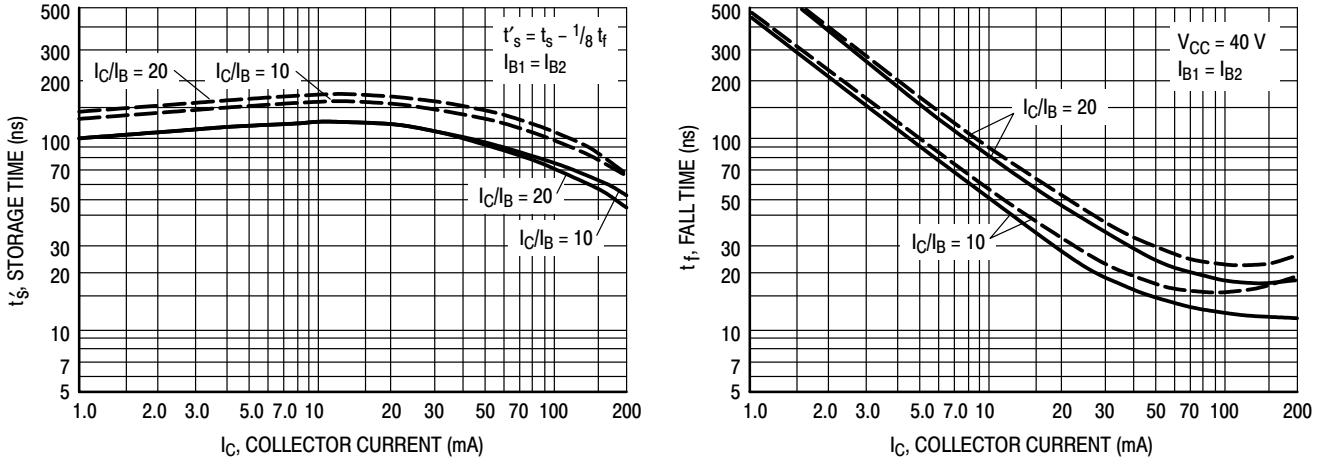


Figure 7. Storage Time

Figure 8. Fall Time

TYPICAL AUDIO SMALL−SIGNAL CHARACTERISTICS
NOISE FIGURE VARIATIONS

(V_{CE} = 5.0 Vdc, T_A = 25°C, Bandwidth = 1.0 Hz)

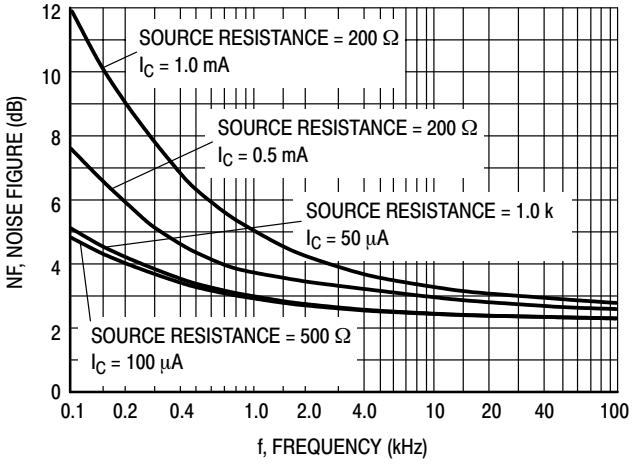


Figure 9.

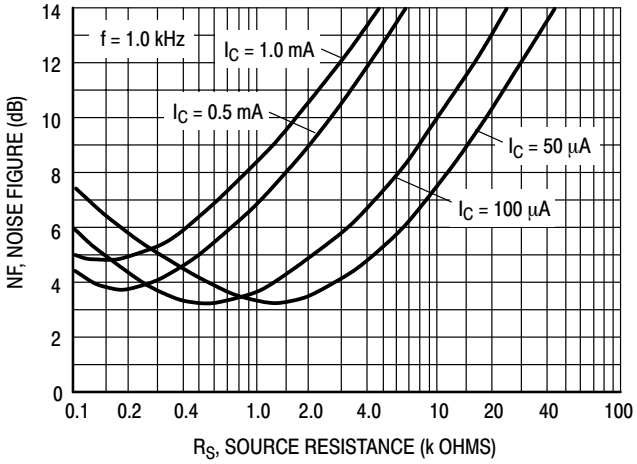


Figure 10.

h PARAMETERS

(V_{CE} = 10 Vdc, f = 1.0 kHz, T_A = 25°C)

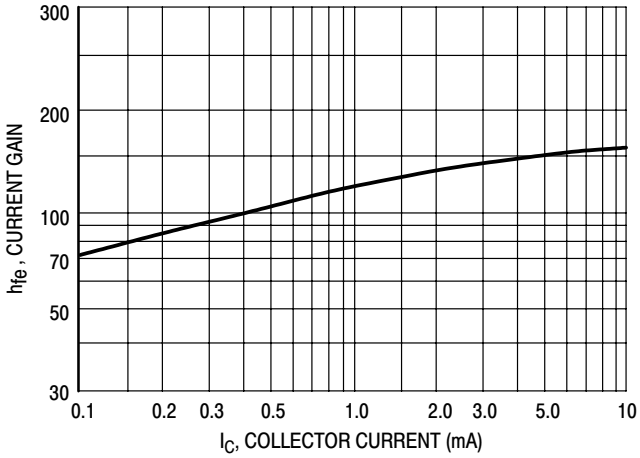


Figure 11. Current Gain

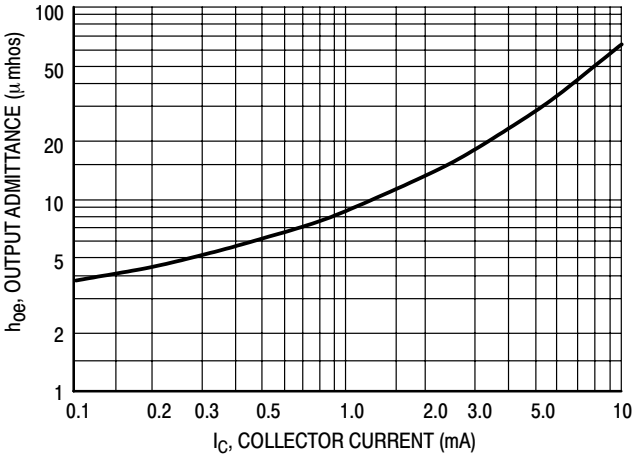


Figure 12. Output Admittance

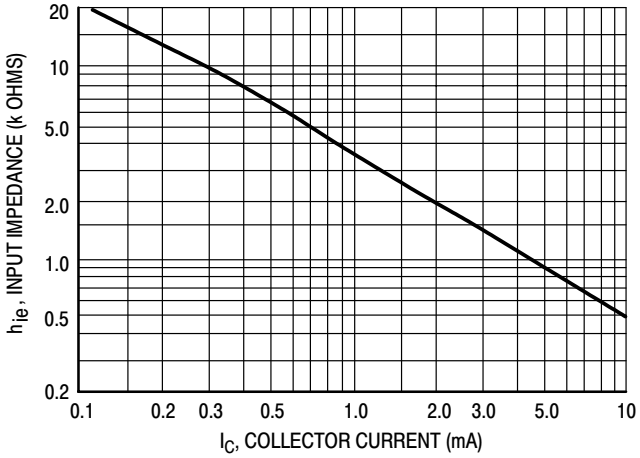


Figure 13. Input Impedance

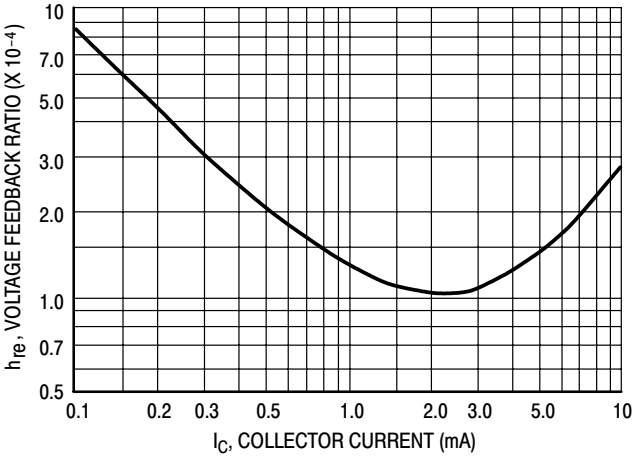


Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

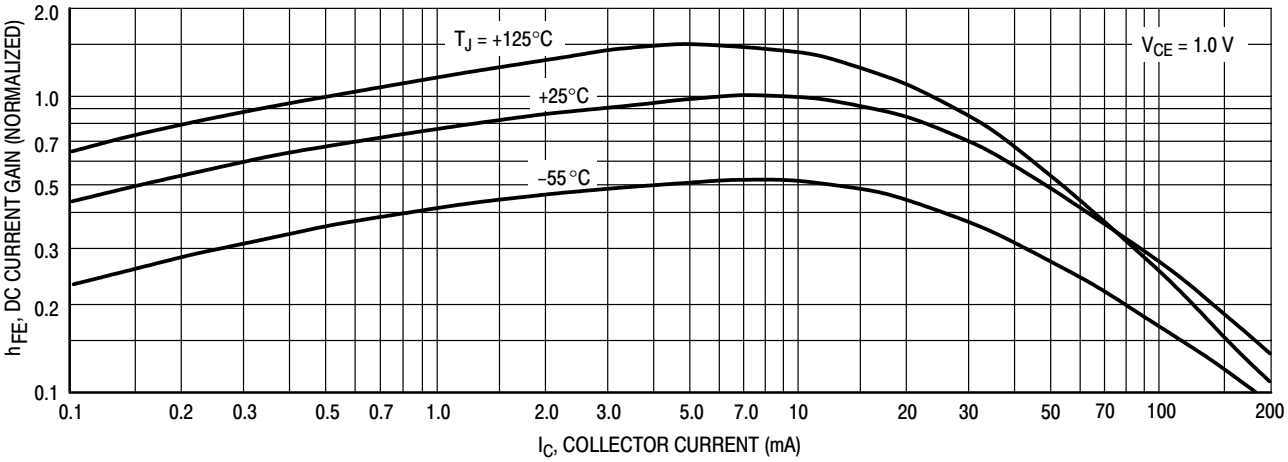


Figure 15. DC Current Gain

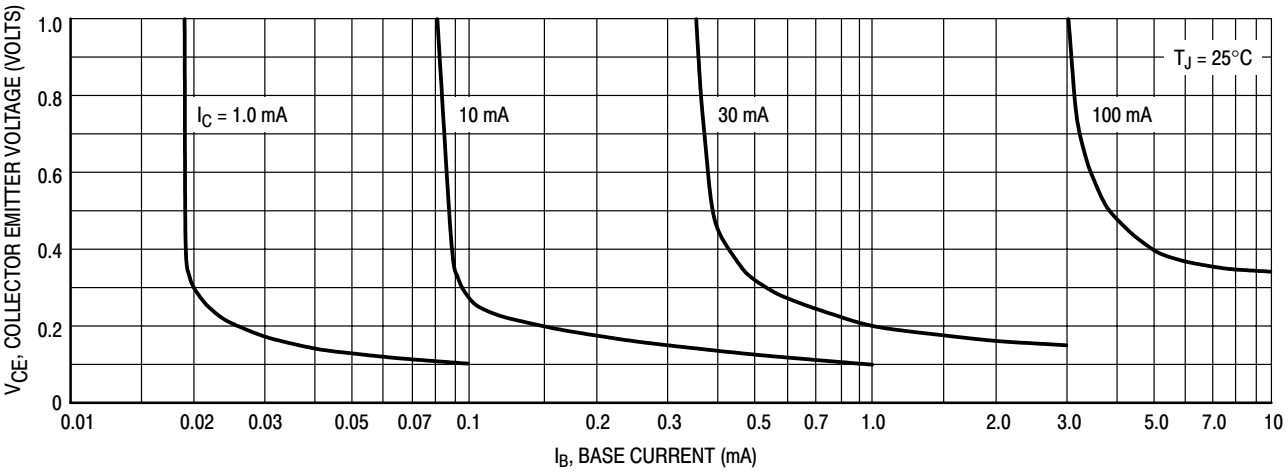


Figure 16. Collector Saturation Region

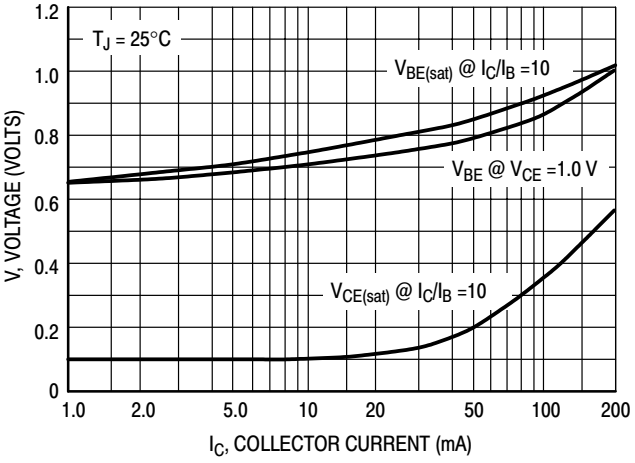


Figure 17. “ON” Voltages

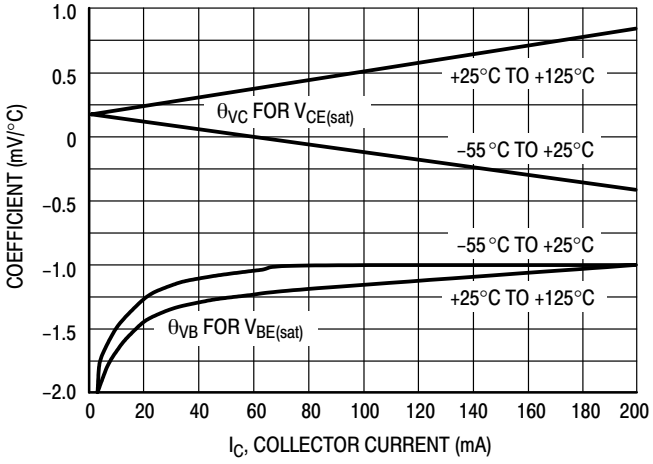
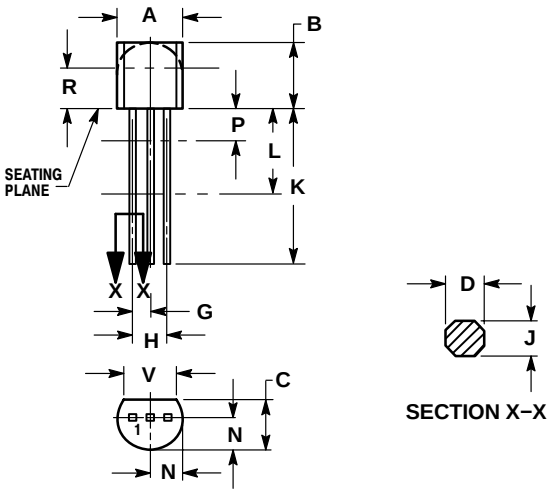


Figure 18. Temperature Coefficients

PACKAGE DIMENSIONS

TO−92
TO−226AA
CASE 29−11
ISSUE AL



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 14:
PIN 1. EMITTER
2. COLLECTOR
3. BASE

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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2N3903/D